Preferred Device

# **NPN Silicon Transistor**

### **Features**

• Pb-Free Packages are Available

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	300	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	300	Vdc
Collector - Emitter Voltage	V <sub>CER</sub>	300	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current	I <sub>C</sub>	100	mAdc
Total Power Dissipation up to T <sub>A</sub> = 25°C	P <sub>D</sub>	1.5	W
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Junction Temperature	TJ	150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

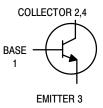
1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in<sup>2</sup>.



### ON Semiconductor®

http://onsemi.com

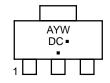
# NPN SILICON TRANSISTOR SURFACE MOUNT







SOT-223 (TO-261) CASE 318E STYLE 1



A = Assembly Location

/ = Year

V = Work Week

DC = Device Code ■ Pb–Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BF720T1	SOT-223	1000 / Tape & Reel
BF720T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
BF720T3	SOT-223	4000 / Tape & Reel
BF720T3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

# 

Characteristics	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	300	_	Vdc	
Collector-Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	V <sub>(BR)</sub> CBO	300	_	Vdc	
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 100 $\mu$ Adc, R <sub>BE</sub> = 2.7 k $\Omega$ )	V <sub>(BR)CER</sub>	300	_	Vdc	
Emitter-Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	_	Vdc	
Collector-Base Cutoff Current $(V_{CB} = 200 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	_	10	nAdc	
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 250 Vdc, R <sub>BE</sub> = 2.7 k $\Omega$ ) (V <sub>CE</sub> = 200 Vdc, R <sub>BE</sub> = 2.7 k $\Omega$ , T <sub>J</sub> = 150°C)	I <sub>CER</sub>	- -	50 10	nAdc μAdc	
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 25 mAdc, V <sub>CE</sub> = 20 Vdc)	h <sub>FE</sub>	50	_	_	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 5.0 mAdc)	V <sub>CE(sat)</sub>	_	0.6	Vdc	
DYNAMIC CHARACTERISTICS	<b>'</b>	•	1		
Current-Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 35 MHz)	f⊤	60	-	MHz	
Feedback Capacitance (V <sub>CE</sub> = 30 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>re</sub>	-	1.6	pF	

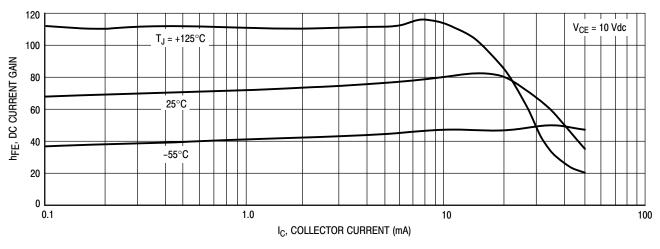


Figure 1. DC Current Gain

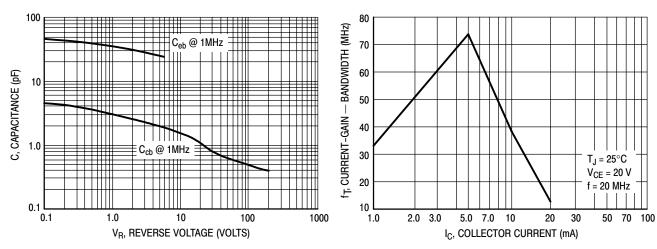
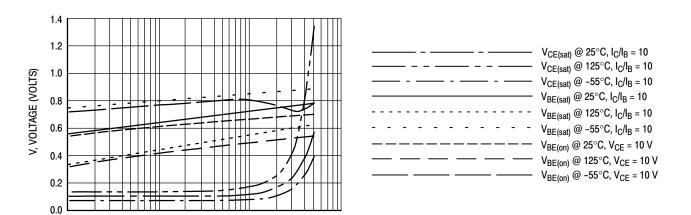


Figure 2. Capacitance



100

Figure 3. Current-Gain - Bandwidth

I<sub>C</sub>, COLLECTOR CURRENT (mA)

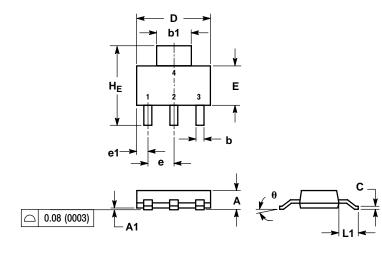
Figure 4. "ON" Voltages

1.0

0.1

### PACKAGE DIMENSIONS

**SOT-223 (TO-261)** CASE 318E-04 ISSUE L



#### NOTES:

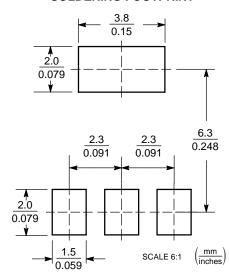
- 1. DIMENSIONING AND TOLERANCING PER ANSI
  - Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1: PIN 1 BASE

- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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